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Delay circuit

Abstract:

A delay circuit having two or more first switching transistors (51,52) connected in series between an output terminal (OUT) and a power source line (Vcc), and two or more second switching transistors (53,54) connected in series between the output terminal (OUT) and another power source line (Vss), the first and the second switching transistors operating in a complementary manner in response to an input signal (IN), one or more pairs of nodes (N5,N7) of the switching transistors being connected by one or more current paths (55) each connected to at least one capacitor (C3,C6) whereby an input signal is transmitted to the output terminal (OUT) at a specified interval defined by the capacitance of the or each capacitor.

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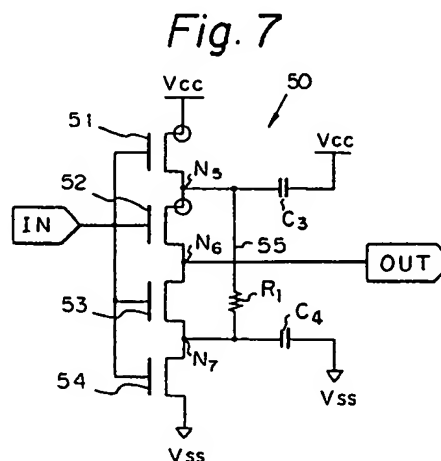
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54 Delay circuit.

57 A delay circuit having two or more first switching transistors (51,52) connected in series between an output terminal (OUT) and a power source line (Vcc), and two or more second switching transistors (53,54) connected in series between the output terminal (OUT) and another power source line (Vss), the first and the second switching transistors operating in a complementary manner in response to an input signal (IN), one or more pairs of nodes (N₅,N₇) of the switching transistors being connected by one or more current paths (55) each connected to at least one capacitor (C₃,C₅) whereby an input signal is transmitted to the output terminal (OUT) at a specified interval defined by the capacitance of the or each capacitor.



DELAY CIRCUIT

The present invention relates to a delay circuit.

Generally, in digital circuits, it is frequently necessary to change the transmission time of the signal, i.e., a plurality of signals should be transmitted at the same time or should be transmitted at predetermined intervals, and a digital circuit is used for transmitting the signals at predetermined intervals.

Known existing delay circuits are composed of switching transistors, such as FET's. Figures 1, 2, 3, and 4 show typical existing delay circuits composed of FET's, and to delay the signal, a Schmitt trigger circuit is used in the circuit of Fig. 1 and 2, a network of capacitors and resistors (CR network) is used in the circuit of Fig. 3, and a multistage inverter circuit is used in the circuit of Fig. 4. Note, the FET's marked o in the drawings are P-channel FET's.

In the circuit of Fig. 1, the Schmitt trigger circuit 10 is composed of two P-channel FET's 11, 12 and two N-channel FET's 13, 14. The P-channel FET 11 and N-channel FET's 13 and 14 are connected in series between a high level constant power supply Vcc and a low level constant power supply Vss. The P-channel FET 12 is connected between the high level constant power supply Vcc and a node N₂, which serves as a connecting point for the N-channel FET's 13 and 14. The gates of the FET's 11, 12, 13, and 14 are connected to the input terminal IN, and a node N₁ is connected to the output terminal OUT of the Schmitt trigger circuit 10.

When the input terminal IN is low level, the P-channel FET's 11 and 12 are ON (conduction occurs between the source and drain) and the N-channel FET's 13 and 14 are OFF (no conduction occurs between the source and drain), and thus the nodes N₁ and N₂ are high level. When the level changes from low level to high level at the input terminal IN, the P-channel FET's 11 and 12 become OFF and the N-channel FET 14 becomes ON immediately the input level passes the threshold voltage, but the N-channel FET 13 cannot become ON at the same time because the nodes N₁ and N₂ are both high level. The N-channel FET 13 becomes ON after the node N₂ is connected to the low level constant power supply Vss through the N-channel FET 14 and the level thereof becomes low. A delay occurs while the node N₂ is changed from high level to low level, which supplies the threshold voltage to the gate of FET 13 after the N-channel FET 14 becomes ON. When the N-channel FET 13 becomes ON, the level of the output terminal OUT is changed from high level to low level. Accordingly, the change of the level from low to high at

the input terminal IN is transmitted to the output terminal OUT in the opposite direction at a predetermined interval.

In Fig. 2, the Schmitt trigger circuit 20 is composed of two P-channel FET's 21 and 22 and two N-channel FET's 23 and 24. The P-channel FET's 21 and 22 and N-channel FET 23 are connected in series between a high level constant power supply Vcc and a low level constant power supply Vss. The N-channel FET 24 is connected between the low level constant power supply Vcc and a node N₃ which serves as a connecting point for the P-channel FET's 21 and 22. The gates of the FET's 21, 22, 23, and 24 are connected to the input terminal IN, and a node N₄ is connected to the output terminal OUT of the Schmitt trigger circuit 20.

When the input terminal IN is high level, the N-channel FET's 23 and 24 are ON and the P-channel FET's 21 and 22 are OFF, and the nodes N₃ and N₄ are low level. When the level changes from high level to low level at the input terminal IN, the N-channel FET's 22 and 23 immediately become OFF and the P-channel FET 21 becomes ON, but the P-channel FET 22 cannot become ON immediately because the nodes N₃ and N₄ are both low level. Therefore, the P-channel FET 22 becomes ON after the node N₃ is connected to the high level constant power supply Vcc through the P-channel FET 21 and the level thereof becomes high. A delay occurs while that the node N₃ is changed from low level to high level after the P-channel FET 21 becomes ON. When the P-channel FET 22 becomes ON, the level of the output terminal OUT is changed from low level to high level, then in the same way as described in Fig. 1, the change of the level from high to low at the input terminal IN is transmitted to the output terminal OUT in the opposite direction at a predetermined interval.

In Fig. 3, the delay circuit 30 is composed of two inverters 31 and 33, and a CR network 32. Each of the inverters 31 and 33 comprises a P-channel FET and an N-channel FET connected in series between a high level constant power supply Vcc and a low level constant power supply Vss. The CR network 32 comprises two capacitors C₁ and C₂, and a resistor R.

When the input signal is low level, the input signal to the CR network is high level, and accordingly the capacitor C₂ is charged and the capacitor C₁ is discharged. When the signal changes from low level to high level at the input terminal IN, the signal at the output of the inverter 31 is changed from high level to low level, thereby discharging

the capacitor C_2 and charging the capacitor C_1 . As a result, the signal input to the CR network 32 is sent to the output of the CR network 32 after a predetermined delay, in accordance with the time constant defined by capacitors C_1 and C_2 , and the resistor R . This delayed signal is then inverted by the inverter 33. When the signal changes from high level to low level, the delay operation in this circuit 30 is also carried out, and accordingly, the signal to the input terminal IN is transmitted to the output terminal OUT at a predetermined interval.

In Fig. 4, the delay circuit 40 is composed of a multistage inverter, i.e., the delay circuit 40 comprises a plurality of inverters 41, 42, ..., 4n. Each inverter comprises a P-channel FET and an N-channel FET connected in series between a high level constant power supply V_{cc} and a low level constant power supply V_{ss} . In this delay circuit 40, a signal input to the input terminal IN is delayed by each inverter circuit, due to a switching time lag thereof. The delay time is defined by the number of inverters in the delay circuit 40.

In the delay circuit shown in Figs. 1 and 2, the delay operation can be carried out for a one way change of the input signal. Namely, the Schmitt trigger circuit 10 shown in Fig. 1 delays the input signal only upon a change from low level to high level, and the Schmitt trigger circuit 20 shown in Fig. 2 delays the input signal only upon a change from high level to low level. Figures 5A, 5B, and 5C shown waveforms for explaining the operation of the delay circuit as shown in Figs. 1 and 2 when the voltage of the high level constant power supply V_{cc} is 5 V. In Fig. 5A, the waveform indicates a signal input to the input terminal IN of the circuits 10 and 20. The input signal changes at time t_1 and time t_2 . In Fig. 5B, the waveform indicates a signal output from the output terminal OUT of the circuit 10, and in Fig. 5C, the waveform indicates a signal output from the output terminal OUT of the circuit 20. Figure 6A, 6B, and 6C show waveforms for explaining the operation of the delay circuit as shown in Figs. 1 and 2 when the voltage of the high level constant power supply V_{cc} is less than 3 V, for example, 1.5 V. In Fig. 6A, the waveform indicates a signal input to the input terminal IN of the circuits 10 and 20. The input signal changes at a time t_1 and time t_2 . In Fig. 6B, the waveform indicates a signal output from the output terminal OUT of the circuit 10, and in Fig. 6C, the waveform indicates a signal output from the output terminal OUT of the circuit 20. From Figs. 5B, 5C, 6B, and 6C, it is clearly understood that the circuit 10 shown in Fig. 1 delays the input signal only upon a change from low level to high level, and the circuit 20 shown in Fig. 2 delays the input signal only upon a change from high level to low level.

In the delay circuit shown in Fig. 3, a delay

operation can be carried out for a rising or falling input signal at the input terminal IN, as shown in Figs. 5A and 5D, when the voltage of the high level constant power supply V_{cc} is 5 V. Conversely, in the delay circuit shown in Fig. 3, the delay time is not stable when the voltage of the high level constant power supply V_{cc} is less than 3 V, for example, 1.5 V, because the response of the CR network is blunted under the low voltage condition, as shown in Fig. 6D. Further, when the response of the CR network is blunted, a wave shaping circuit must be included for compensating the weakened output signal.

In the delay circuit shown in Fig. 4, however, defects described above do not exist, but instead, it is necessary to accumulate among inverters on the semiconductor tip to obtain a predetermined interval, because the delay at each inverter is very slight, and thus the circuit scale is increased. Further, an increase in the number of inverters leads to an increase in the power consumption.

According to the present invention, delay circuit is composed of a first switching transistor and a second switching transistor operable in a complementary manner in response to an input signal, an output terminal connected to the node of the first switching transistor and the second switching transistor, one or more switching transistors of the same type as the first switching transistor provided between the first switching transistor and a power source, one or more switching transistors of the same type as the second switching transistor provided between the second switching transistor and another power source, at least one current path connecting at least one pair of nodes, one of which nodes being located between the first switching transistor and the power source and the other node being located between the second switching transistor and the other power source, and one or more capacitors connected to the current path.

An embodiment of the present invention may provide a delay circuit in which the output signal is delayed by a specified time interval with respect to the input of both a rising edge and a falling edge, and able to work reliably and to obtain a sufficient delay time at a low power source voltage.

An embodiment of the present invention may provide a small-scale delay circuit having a low power consumption, a stable delay time regardless of changes in the direction of the voltage at the input terminal, and able to operate reliably and to obtain a sufficient delay time at a lower power source voltage.

Reference is made, by way of example, to the accompanying drawings in which:-

Fig. 1 is a circuit diagram of an existing delay circuit including a Schmitt trigger circuit;

Fig. 3 is a circuit diagram of an existing delay circuit including a network of capacitors and a resistor;

Fig. 4 is a circuit diagram of an existing delay circuit including multistage inverters;

Figs. 5A, 5B, 5C, 5D, 5E, and 5F are waveform diagrams showing waveforms of the existing circuits and of the present invention when the voltage of a high level constant power supply V_{cc} is 5 V, for explaining the operation of the existing circuits and those of the present invention;

Figs. 6A, 6B, 6C, 6D, 6E, and 6F are waveform diagrams including waveforms of the existing circuits and of the present invention when the voltage of a high level constant power supply V_{cc} is 1.5 V, for explaining the operation of the existing circuits and those of the present invention;

Fig. 7 is a circuit diagram of a first embodiment of a delay circuit according to the present invention;

Figs. 8A and 8B are circuit diagrams of Fig. 7 showing a delay operation when the input signal is changed from high level to low level;

Figs. 8C and 8D are circuit diagrams of Fig. 7 showing a delay operation when the input signal is changed from low level to high level;

Fig. 9 is a circuit diagram of a modification of the first embodiment shown in Fig. 7;

Fig. 10A is a waveform diagram of the delay circuit shown in Figs. 7 and 9, for explaining the operation of the delay circuits when the time constant value is small;

Fig. 10B is a waveform diagram of the delay circuit shown in Figs. 7 and 9, for explaining the operation of the delay circuits when the time constant value is large;

Fig. 11 is a circuit diagram of a second embodiment of a delay circuit according to the present invention;

Fig. 12 is a circuit diagram of a third embodiment of a delay circuit according to the present invention;

Fig. 13 is a circuit diagram of a modification of the third embodiment as shown in Fig. 12;

Fig. 14 is a circuit diagram of a fourth embodiment of a delay circuit according to the present invention;

Fig. 15 is a circuit diagram of a fifth embodiment of a delay circuit according to the present invention;

Fig. 16 is a circuit diagram of a modification of the fifth embodiment as shown in Fig. 15; and

Fig. 17 is a circuit diagram of another modification of the fifth embodiment as shown in Fig. 15.

Figure 7 is a circuit diagram of a first embodiment of a delay circuit 50 according to the present

invention. The delay circuit 50 is composed of two P-channel FET's 51 and 52, two N-channel FET's 53 and 54, two capacitors C_3 and C_4 , and a resistor R_1 . The P-channel FET's 51 and 52, and N-channel FET's 53 and 54 are connected in series between a high level constant power supply V_{cc} and a low level constant power supply V_{ss} . The gates of the FET's 51, 52, 53, and 54 are connected to an input terminal IN, and a node N_5 and a node N_7 are connected by a current path 55 having the resistor R_1 arranged therein. A node N_6 is connected to an output terminal OUT. Further, the capacitor C_3 is connected to a point in the current path 55, between the node N_5 and the resistor R_1 , and the capacitor C_4 is connected to a point in current path 55 between the node N_7 and the resistor R_1 . The free terminal of the capacitor C_3 is connected to the high level constant power supply V_{cc} , and the free terminal of the capacitor C_4 is connected to the low level constant power supply V_{ss} .

When metal-oxide-semiconductor field effect transistors (MOSFET) are employed as the FET's 51, 52, 53, and 54, the capacitors C_3 and C_4 are formed also by MOSFET's by connecting the source and the drain thereof. Namely, if the source and the drain of a MOSFET are connected to the high level constant power supply V_{cc} and a gate of the MOSFET is connected to the current path 55 between the node N_5 and the resistor R_1 , the MOSFET acts as the capacitor C_3 .

Figures 8A, 8B, 8C, and 8D explain the operation of the delay circuit 50 shown in Fig. 7. In Fig. 8A, the signal input to the input terminal IN shown in Fig. 7 is high level "H". Under this condition, the P-channel FET's 51 and 52 are OFF, and the N-channel FET's 53 and 54 are ON, and the nodes N_5 , N_6 , and N_7 are all low level "L", whereby the capacitor C_3 is charged and the capacitor C_4 is discharged.

When the signal input to the input terminal IN changes from high level "H" to low level "L", as shown in Fig. 8B, the P-channel FET 51 becomes ON immediately the input level becomes lower than the threshold voltage, and the N-channel FET's 53 and 54 become OFF immediately the input level becomes lower than the threshold voltage. The P-channel FET 52, however, cannot become ON at this time because the nodes N_5 and N_6 are still low level. When the P-channel FET 51 is turned ON, current flows through the FET 51, and a current I_1 discharges the capacitor C_3 , and at the same time, a current I_2 flows through the resistor R_1 to charge the capacitor C_4 . After the capacitor C_3 is discharged and the capacitor C_4 is charged, the voltage level at the node N_5 is pulled up to high level "H", the P-channel FET 52 is turned ON, and current flows through the FET 52

to change the voltage at the output terminal OUT from low level "L" to high level "H". Accordingly, when the input signal level is changed from high "H" to low "L", the level of the output signal is changed from low "L" to high "H" after a specified interval defined by the capacity of the capacitors C_3 and C_4 . When the P-channel FET's 51 and 52 are ON, the N-channel FET's 53 and 54 are OFF, the nodes N_5 , N_6 , and N_7 are all at high level "H", and the capacitor C_3 is charged and the capacitor C_4 is discharged, as shown in Fig. 8C.

Conversely, when the signal input to the input terminal IN is changed from low level "L" to high level "H" as shown in Fig. 8D, the N-channel FET 54 becomes ON immediately the input level exceeds the threshold voltage, and the P-channel FET's 51 and 52 become OFF immediately the input exceeds the threshold voltage. The N-channel FET 53, however, cannot become ON at the same time because the nodes N_6 and N_7 are both high level. When the N-channel FET 54 is turned ON, current flow through the FET 54, and a current I_3 discharge the capacitor C_4 , and at the same time, a current I_4 flows through the resistor R_1 to charge the capacitor C_3 . After the capacitor C_4 is discharged and the capacitor C_3 is charged, the voltage level at the node N_7 is pulled down to low level "L", the N-channel FET 53 is turned ON, and current flows through the FET 53 to change the voltage at the output terminal OUT from high level "H" to low level "L". Accordingly, when the level of the input signal changes from low "L" to high "H", the level of the output signal is changed from high "H" to low "L" after a specified interval defined by the capacity of the capacitors C_3 and C_4 . When the P-channel FET's 51 and 52 are OFF, the N-channel FET's 53 and 54 are ON, the nodes N_5 , N_6 , and N_7 are all at low level "L", and the capacitor C_3 is discharged and the capacitor C_4 is charged, as shown in Fig. 8A.

Figure 9 is a circuit diagram of a modification of the first embodiment shown in Fig. 7. In Fig. 9, the delay circuit 50 is also composed of two P-channel FET's 51 and 52, two N-channel FET's 53 and 54, two capacitors C_3 and C_4 , and a resistor R_1 , and the connections therebetween are the same as for the delay circuit 50 shown in Fig. 7, except for the connection of the free terminals of the capacitors C_3 and C_4 . Namely, the free terminal of the capacitor C_3 is connected to the low level constant power supply V_{SS} and the free terminal of the capacitor C_4 is connected to the high level constant power supply V_{CC} in this embodiment, but the free terminal of the capacitor C_3 is connected to the high level constant power supply V_{CC} and the free terminal of the capacitor C_4 is connected to the low level constant power supply V_{SS} in Fig. 7. In this modification, the delay opera-

tion of the circuit 50' is the same as the operation of the delay circuit 50 shown in Fig. 7, except that the charge and discharge operations of the capacitors C_3 and C_4 are reversed.

Figure 10A is a waveform diagram of the delay circuit shown in Figs. 7 and 9, for explaining the operation of the delay circuits when the time constant value decided by the capacitance of the capacitors C_3 and C_4 and the resistance of the resistor R_1 is small. When the level of the input terminal IN changes from high level "H" to low level "L", as indicated by the reference numeral X in Fig. 10A, the level of the node N_5 changes from low level "L" to high level "H", as indicated by the reference numeral Y, in accordance with the small time constant. In the process of an increment of the level of the node N_5 , the P-channel FET 52 turns ON when the level of the node N_5 exceeds the threshold level V_T . After the FET 52 is turned ON, the level of the output terminal OUT is changed from low level "L" to high level "H", as indicated by the reference numeral Z.

Figure 10B is a waveform diagram of the delay circuit shown in Figs. 7 and 9, for explaining the operation of the delay circuits when the time constant value is large. Under this circumstance, when the level of the input terminal IN changes from high level "H" to low level "L", as indicated by the reference numeral S in Fig. 10B, the level of the node N_5 slowly changes from low level "L" to high level "H" as indicated by the reference numeral T, in accordance with the large time constant. In the process of a slow increment of the level of the node N_5 , the P-channel FET 52 turns ON when the level of the node N_5 exceeds the threshold level V_T . After the FET 52 is turned ON, the level of the output terminal OUT changed from low level "L" to high level "H" as indicated by the reference numeral U at the same speed as that when the time constant value is small.

Returning to Figs. 5A to 5F, Figs. 5A and 5E show waveforms for explaining the operation of the delay circuit of the present invention as shown in Figs. 7 and 9 when the voltage of the high level constant power supply V_{CC} is 5 V. The waveform in Fig. 5E indicates a signal output from the output terminal OUT of the circuit 50 and 50' when the input signal at the input terminal IN of the circuits 50 and 50' changes at a time t_1 and time t_2 . Returning to Figs. 6A to 6F, Figs. 6A and 6E show waveforms for explaining the operation of the delay circuit as shown in Figs. 7 and 9 when the voltage of the high level constant power supply V_{CC} is less than 3 V, for example, 1.5 V. The waveform in Fig. 6E indicates a signal output from the output terminal OUT of the circuit 50 and 50' when the input signal at the input terminal IN of the circuits 50 and 50', changes at a time t_1 and time t_2 . Comparing

Figs. 5E and 6E, it can be clearly understood that the time delay by the delay circuits 50 and 50' when the voltage of the high level constant power supply V_{cc} is 1.5 V, is longer than the time delay by the delay circuits 50 and 50' when the voltage of the high level constant power supply V_{cc} is 5 V, and from Figs. 5E and 6E, it can be understood that the pulling up time or pulling down time at the delay circuits is almost the same.

As described above, the delay circuit in Fig. 7 and 9 transmits the input signal at the input terminal IN to the output terminal OUT at a predetermined interval when the input signal is rising or falling. Further, the delay circuit in Figs. 7 and 9 requires only the capacitors C_3 , C_4 and the resistor R_1 to obtain a reliable delay time, and thus the circuit is kept to a small scale. Further more, the delay circuit in Figs. 7 and 9 operates effectively when the constant power source V_{cc} is at a low level.

Figure 11 is a circuit diagram of a second embodiment of a delay circuit 60 according to the present invention. This delay circuit 60 is composed of two P-channel FET's 61 and 62, two N-channel FET's 63 and 64 connected in series between the low level constant power supply V_{ss} and the high level constant power supply V_{cc} , a current path 65 connecting nodes N_6 and N_9 , a resistor R_2 provided on the current path 65, a capacitor C_5 connected to the current path 65 in parallel to the resistor R_2 , and a node N_9 connected to the output terminal OUT.

In this second embodiment, the operation of the delay circuit 60 is almost the same as the operation of the delay circuit 50 shown in Fig. 7, except for the charge and discharge operation of the capacitor C_5 . When the signal input to the input terminal IN is high level "H", two metal plates of the capacitor C_5 are given a negative electric charge because the nodes N_6 and N_7 are both low level. When the signal input to the input terminal IN is low level "L", the two metal plates of the capacitor C_5 are given a positive electric charge because the nodes N_6 and N_7 are both high level. Accordingly, the charge and discharge operation of the capacitor C_5 , which decides the delay time at the delay circuit 60, occurs at the transition of the input signal. The waveform-characteristics of the input terminal IN and the output terminal OUT are shown in Figs. 5A and 5F (when the voltage of the high level constant power supply V_{cc} is 5 V), and in Figs. 6A and 6F (when the voltage of the high level constant power supply V_{cc} is 1.5 V). From Figs. 5F and 6F, it is clearly understood that the delay circuit 60 works effectively when the constant power source V_{cc} is at a low level.

Figure 12 is a circuit diagram of a third embodiment of a delay circuit 70 according to the

present invention. This delay circuit 70 is composed of two P-channel FET's 71 and 72, two N-channel FET's 73 and 74 connected in series between the low level constant power supply V_{ss} and the high level constant power supply V_{cc} , a current path 75 connecting nodes N_{11} and N_{13} , resistors R_3 and R_4 connected in series on the current path 75, a capacitor C_6 , and a node N_{12} connected to the output terminal OUT. In this embodiment, the capacitor C_6 is connected to the current path 75 at the point at which the resistor R_3 and R_4 are connected thereto, and the free terminal of this capacitor C_6 is connected to the high level constant power supply V_{cc} . In this third embodiment, operation of the delay circuit 70 is almost the same as the operation of the delay circuit 50 shown in Fig. 7, except for charge and discharge operation of the capacitor C_6 . When the signal input to the input terminal IN is high level "H", the capacitor C_6 is charged because the nodes N_{11} and N_{13} are low level and the constant power supply V_{cc} is high level. When the signal input to the input terminal IN is changed from high level "H" to low level "L", the capacitor C_6 is discharged because the level of the nodes N_{11} and N_{13} is changed from low to high. When the signal input to the input terminal IN is changed from low level "L" to high level "H", the capacitor C_6 is charged because the level of the nodes N_{11} and N_{13} is changed from high to low. Accordingly, the charge and discharge operations of the capacitor C_6 decides the delay time of the delay circuit 70 in accordance with the time constant decided by the capacitance of the capacitor C_6 and the resistance of the resistors R_3 and R_4 .

Figure 13 is a circuit diagram of a modification of the third embodiment as shown in Fig. 12. The construction of the delay circuit 70' is the same as that of the delay circuit 70 shown in Fig. 12, except for the connection of the free terminal of the capacitor C_7 . Namely, the free terminal of the capacitor C_7 is connected to the low level constant power supply V_{ss} in this embodiment, but is connected to the high level constant power supply V_{cc} in Fig. 12. In this modification, the operation of the delay circuit 70' is the same as the operation of the delay circuit 70 shown in Fig. 12, except the charge and discharge operation of the capacitor C_7 are reversed.

Figure 14 is a circuit diagram of a fourth embodiment of a delay circuit according to the present invention. This delay circuit 80 is composed of two P-channel FET's 81 and 82, two N-channel FET's 83 and 84 connected in series between the low level constant power supply V_{ss} and the high level constant power supply V_{cc} , a current path 85 connecting nodes N_{14} and N_{16} , capacitors C_8 and C_9 connected to a different point of the current path 85, and a node N_{15} connected to the

output terminal OUT. In this embodiment, a free terminal of the capacitor C_8 is connected to the high level constant power supply V_{cc} , and a free terminal of the capacitor C_9 is connected to the low level constant power supply V_{ss} . Note, the connection of the free terminals of the capacitors C_8 and C_9 may be reversed. Since the current path itself has a slight line-resistance, the operation of this delay circuit 80 is the same as that of the delay circuit 50 shown in Fig. 7.

As a modification of the delay circuit 80 as shown in Fig. 14, the following circuits (not shown) can be formed: (a) a circuit wherein one of the capacitors C_8 or C_9 is removed from the delay circuit 80; (b) a circuit wherein one or more resistors are provided on the current path 85 of the circuit in Fig. 14 or the circuit described in (a). Further, the part surrounded by a dot-like N_x may be treated as a common node including the nodes N_{14} and N_{16} .

Figure 15 is a circuit diagram of a fifth embodiment of a delay circuit 90 according to the present invention. Three P-channel FET's 91, 92, 93, three N-channel FET's 94, 95, 96, current paths 97 and 98, four capacitors C_{10} , C_{11} , C_{12} , and C_{13} , and resistors R_5 and R_6 are used in the delay circuit 90, and the connection of the FET's 92, 93, 94, 95, the current path 97, the capacitors C_{11} and C_{12} , and the resistor R_6 are the same as for the delay circuit 50 shown in Fig. 7. In this embodiment, the FET 91 is added between the FET 92 and the high level constant power source V_{cc} , the FET 96 is added between the FET 95 and the low level constant power source V_{ss} , a current path 98 provided with a resistor R_5 is added between nodes N_{17} and N_{21} , and capacitors C_{10} and C_{13} are added to the current path 98. The operation of the delay circuit 90 is similar to the delay operation described in Fig. 7, i.e., when the input signal changes from high level "H" to low level "L", the FET's 91, 92, and 93 become ON, in this order, at a predetermined interval therebetween them, and when the input signal changes from low level "L" to high level "H", the FET's 96, 95, and 94 become ON, in this order, also at a predetermined interval therebetween. Accordingly, in the delay circuit 90 shown in Fig. 15, the delay time is longer than that in the delay circuits shown in Figs. 7, 9, 11, 12, 13, and 14.

Figure 16 shows a delay circuit 90' as a modification of the delay circuit 90 shown in Fig. 15. In this embodiment, the connection of the nodes N_{17} , N_{18} , N_{20} and N_{21} are different from those of Fig. 15. Namely, in this embodiment, the nodes N_{17} and N_{20} are connected by a current path 97' and the nodes N_{18} and N_{21} are connected by a current path 98'. The operation of this delay circuit is similar to that of the delay circuit 90 shown in Fig.

15.

Figure 17 shows a delay circuit 90'' as another modification of the delay circuit 90 as shown in Fig. 15. In this embodiment, the current path 97 and capacitors C_{11} and C_{12} are removed from the delay circuit 90 in Fig. 15, and thus the delay time is longer than that in the delay circuit shown in from Figs. 7, 9, 11, 12, 13, and 14 but shorter than that in the delay circuit shown in Figs. 15 and 16.

Claims

1. A delay circuit comprising:

a first switching transistor (52, 62, 72, 82, 93) and a second switching transistor (53, 63, 73, 83, 94) operable in a complementary manner in response to an input signal (IN);

an output terminal (OUT) connected to a node (N_6 , N_9 , N_{12} , N_{15} , N_{19}) of said first switching transistor and said second switching transistor;

one or more switching transistors (51, 61, 71, 81, 91, 92) of the same type as said first switching transistor provided between said first transistor and a power source line;

one or more switching transistors (54, 64, 74, 84, 95, 96) of the same type as said second switching transistor provided between said second transistor and another power source line;

at least one current path (55, 65, 75, 85, 97, 97', 98, 98') connecting at least one pair of nodes (N_5 , N_7 ; N_8 , N_{10} ; N_{11} , N_{13} ; N_{14} , N_{16} ; N_{17} , N_{21} ; N_{18} , N_{20} ; N_{17} , N_{20} ; N_{18} , N_{21}), one of which nodes being located between said first switching transistor and said power source line and the other of said nodes being located between said second switching transistor and said another power source line; and one or more capacitors (C_3 , C_4 , C_5 , C_6 , C_7 , C_8 , C_9 , C_{10} , C_{11} , C_{12} , C_{13}) connected to said current path.

2. A delay circuit as set forth in claim 1, wherein said current path has a resistance.

3. A delay circuit as set forth in claim 1 or 2, wherein a free terminal of the or each capacitor is connected to a power source line having a predetermined potential.

4. A delay circuit as set forth in claim 3, wherein two capacitors (C_3 , C_4 ; C_8 , C_9 ; C_{10} , C_{13} ; C_{11} , C_{12} ; C_{10} , C_{12} ; C_{11} , C_{13}) are connected to the said current path, or to each said current path respectively, a part of said current path between points at which said two capacitors are connected has a predetermined resistance, and the free terminal of each capacitor is connected to a respective one of two different power source lines having different predetermined potentials.

5. A delay circuit as set forth in claim 4, wherein said different power source lines are a positive power source line (Vcc) and a negative power source line (Vss).

6. A delay circuit as set forth in claim 4 or 5, wherein said predetermined resistance is realized by a resistor (R₁, R₂, R₅, R₆, R₇, R₈) provided in said current path.

7. A delay circuit as set forth in claim 3, wherein there is a single capacitor (C₅, C₆, C₇) connected to said current path and with its free terminal connected to a power source line having a predetermined potential.

8. A delay circuit as set forth in claim 7, wherein said current path has a resistance realized by resistors (R₃, R₄) provided on both sides of a point at which said capacitor is connected to said current path.

9. A delay circuit as set forth in claim 7 or 8, wherein said power source line is a positive power source line (Vcc).

10. A delay circuit as set forth in claim 7 or 8, wherein said power source line is a negative power source line (Vss).

11. A delay circuit as set forth in claim 1, or claim 6 as appended to claim 1, wherein said capacitor (C₅) is connected in parallel to said current path (65) and a part of said current path parallel to said capacitor has a predetermined resistance.

12. A delay circuit as set forth in any preceding claim, wherein a single switching transistor (51, 61, 71, 81) of the same type as said first switching transistor is provided between said first transistor and a power source line, a single switching transistor (54, 64, 74, 84) of the same type as said second switching transistor is provided between said second transistor and another power source line, and a single current path (55, 65, 75, 85) connects a pair of nodes (N₅, N₇; N₈, N₁₀; N₁₁, N₁₃; N₁₄, N₁₆), one of said pair of nodes being located between said first switching transistor (52, 62, 72, 82) and said single switching transistor (51, 61, 71, 81) of the same type as said first switching transistor and the other of said pair of nodes being located between said second switching transistor (53, 63, 73, 83) and said single switching transistor (54, 64, 74, 84) of the same type as said second switching transistor.

13. A delay circuit as set forth in any of claims 1 to 6, wherein two switching transistors (91, 92) of the same type as said first switching transistor (93) are provided between said first transistor (93) and a power source line, two switching transistors (95, 96) of the same type as said second switching transistor (94) are provided between said second transistor (94) and another power source line, and one or two current paths (97, 98, 97', 98') connect

a pair of nodes, one of said pair of nodes being located between said first switching transistor (93) and said power source line and the other of said pair of nodes being located between said second switching transistor (94) and said another power source line.

Fig. 1

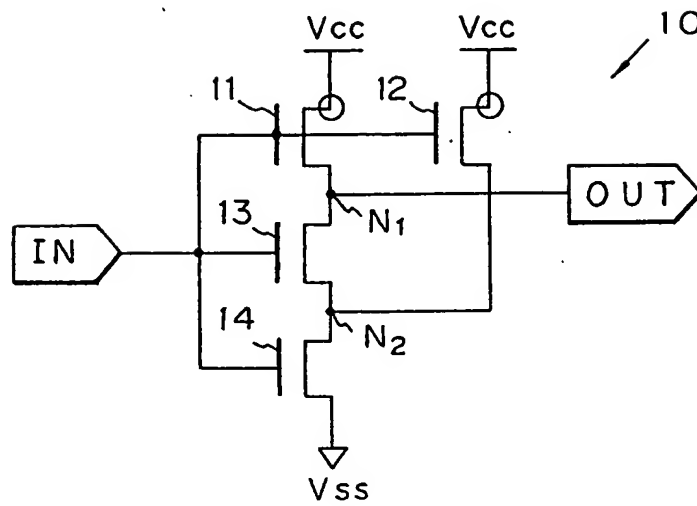


Fig. 2

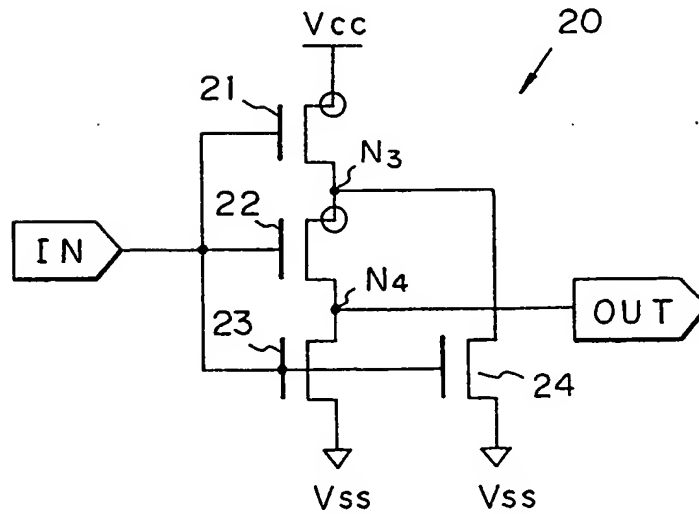


Fig. 3

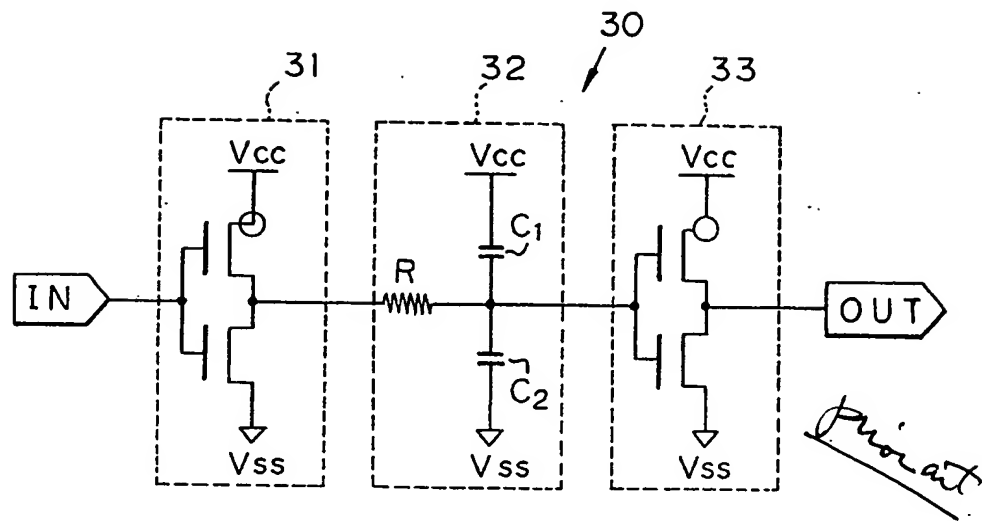
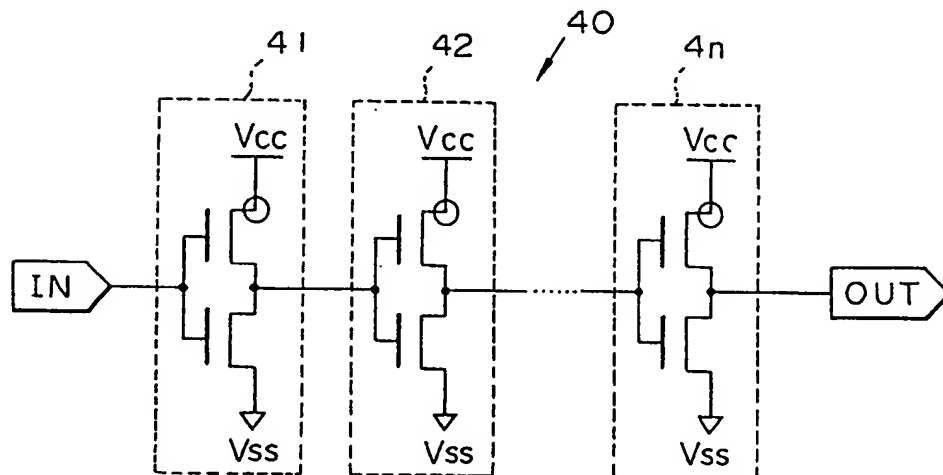
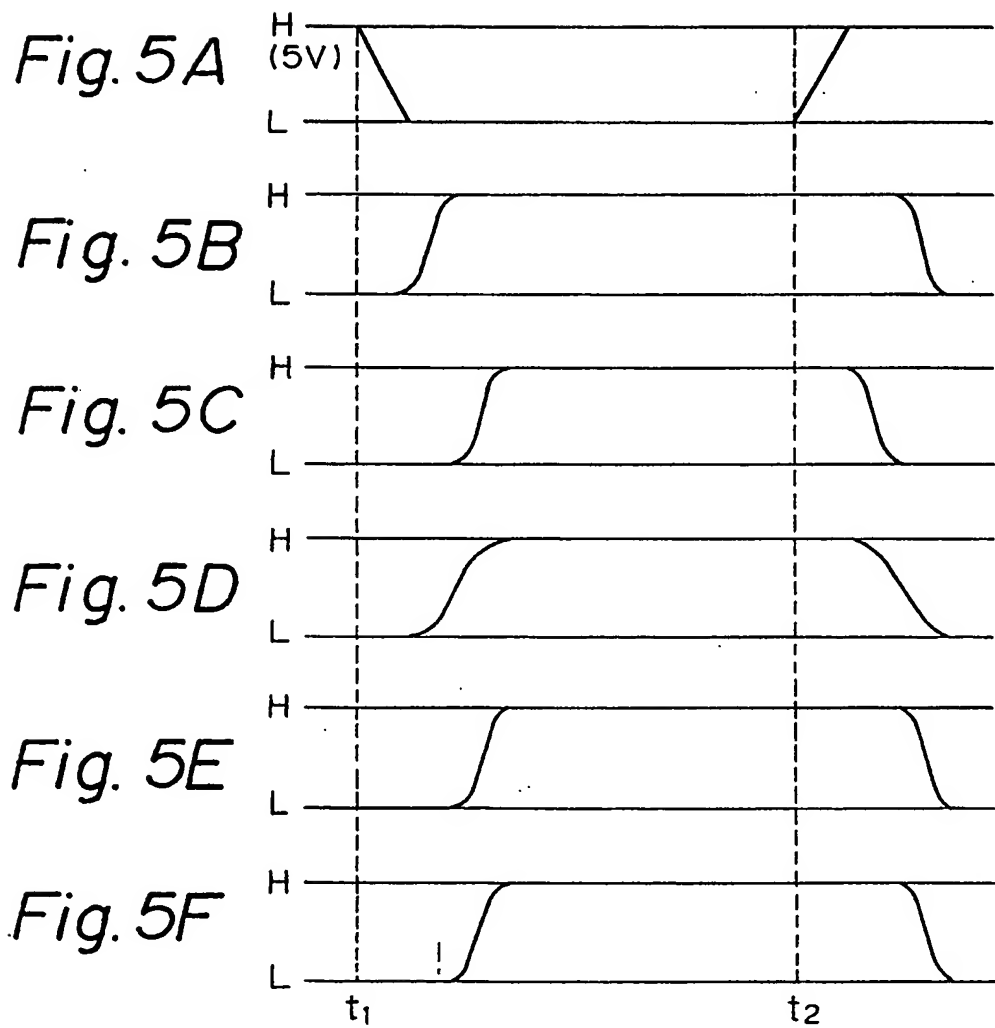


Fig. 4





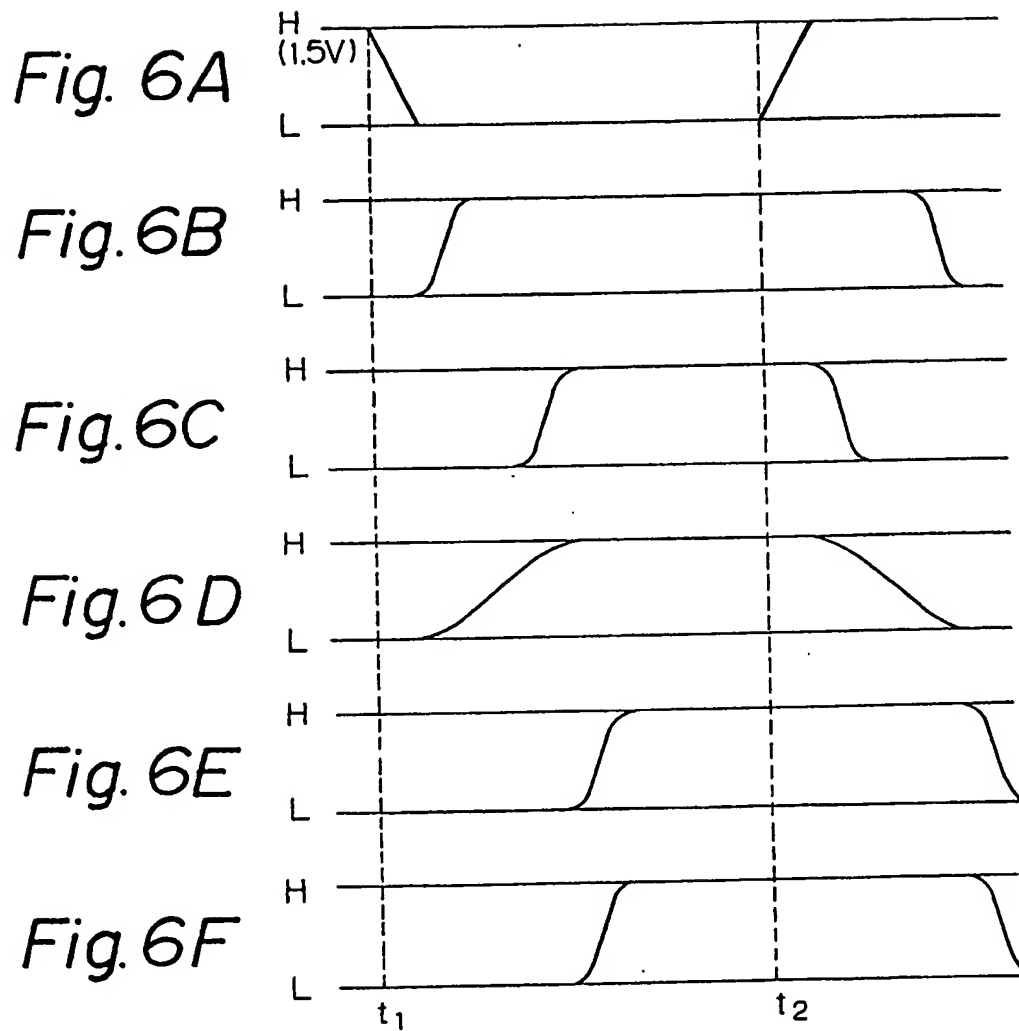


Fig. 7

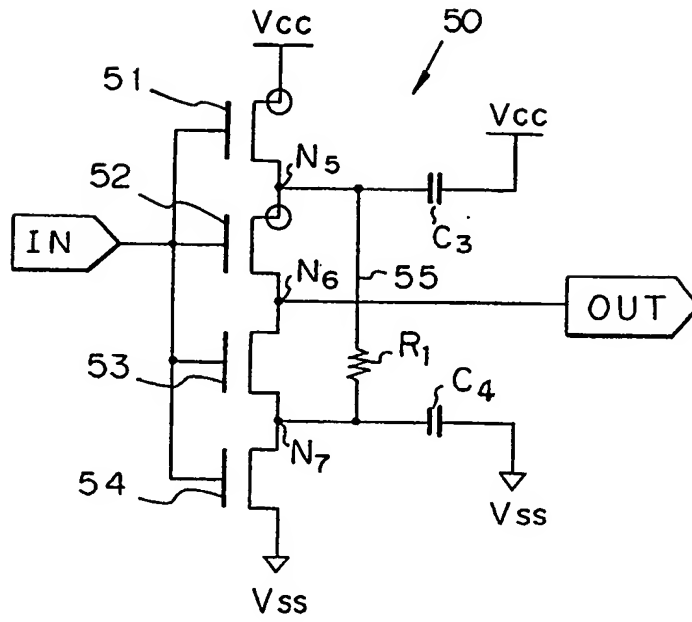


Fig. 8A

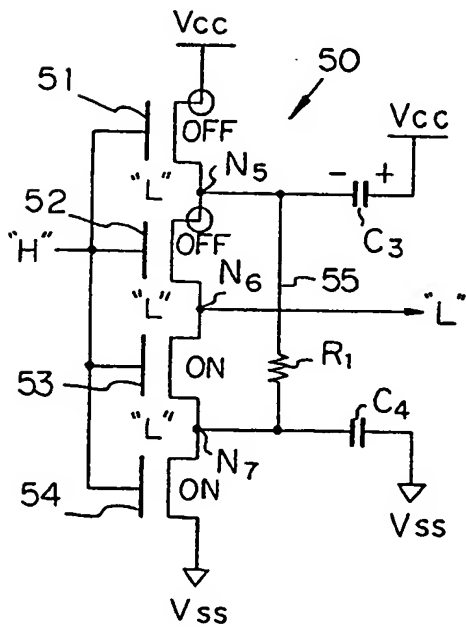


Fig. 8B

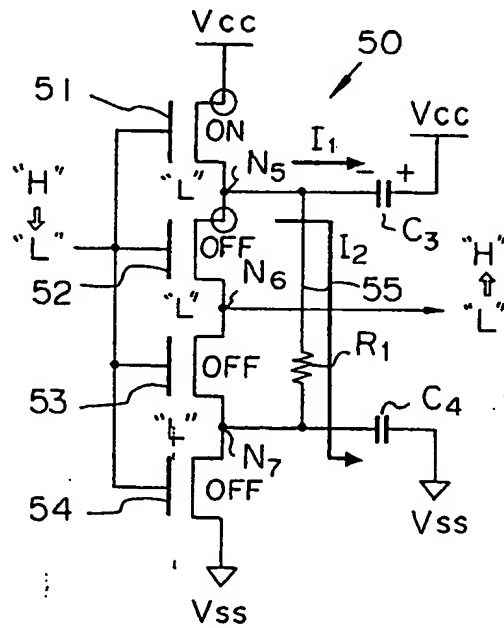


Fig. 8C

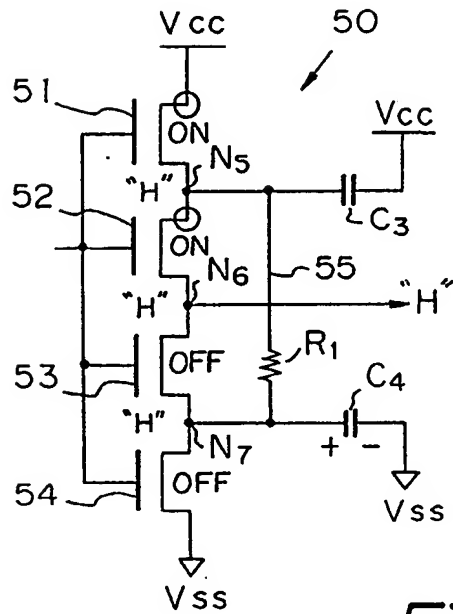


Fig. 8D

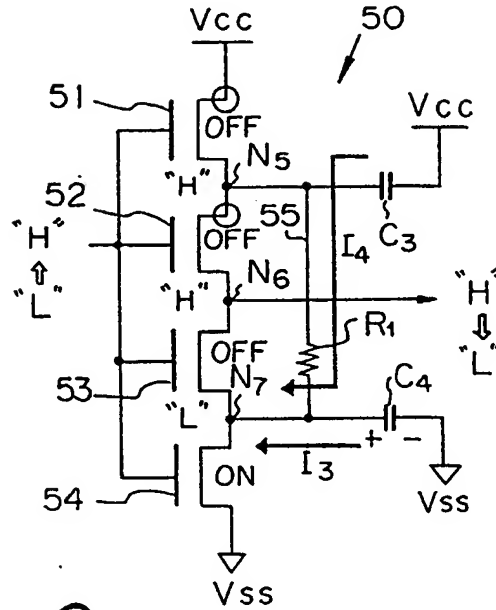


Fig. 9

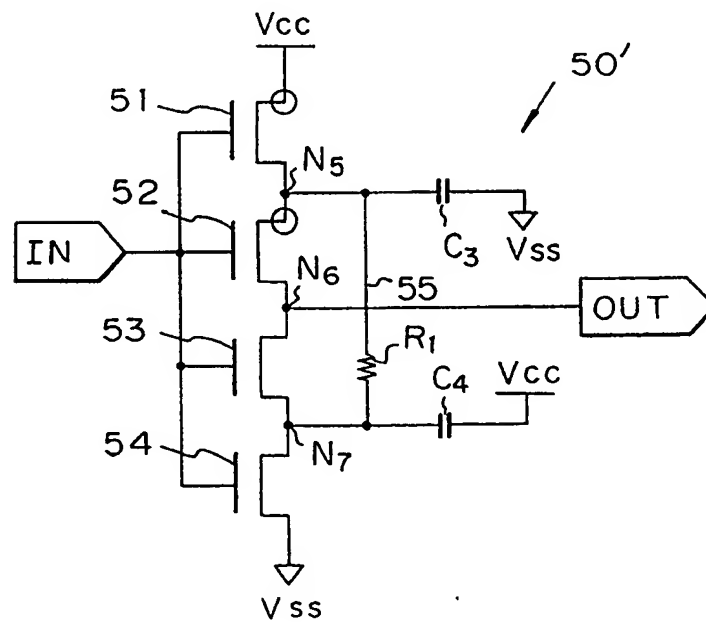


Fig. 10A

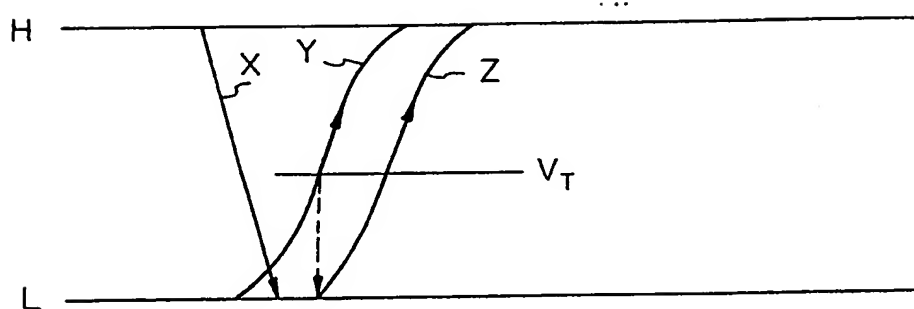


Fig. 10B

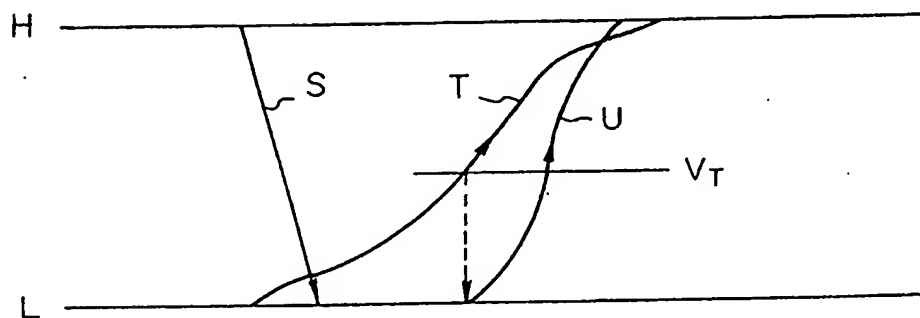


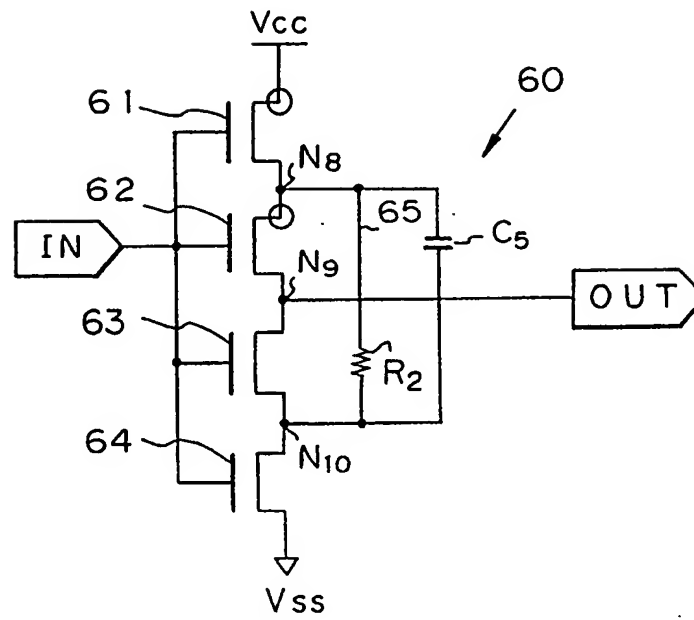
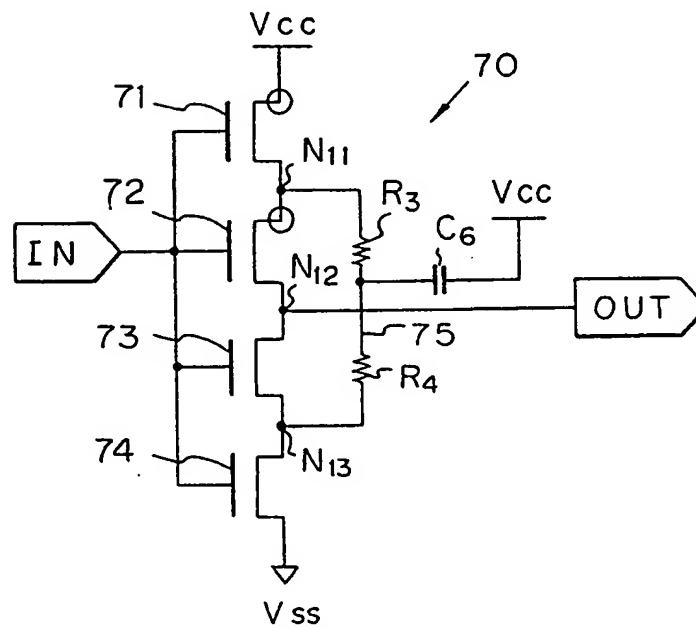
Fig. 11*Fig. 12*

Fig. 13

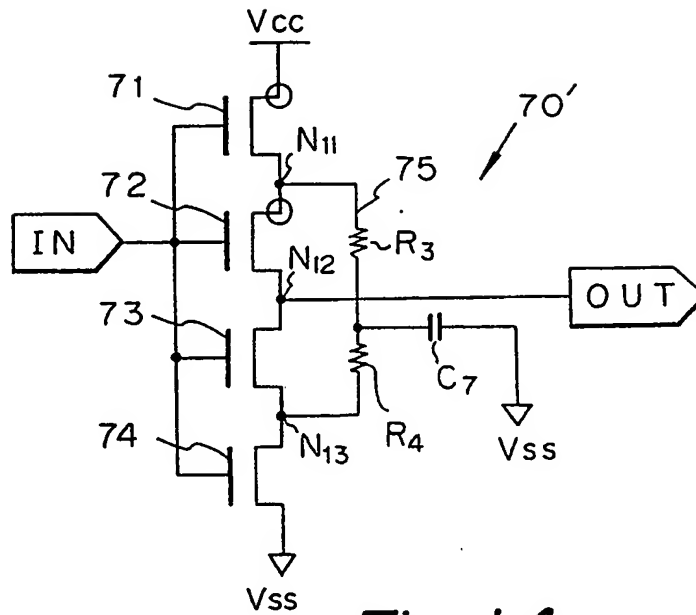


Fig. 14

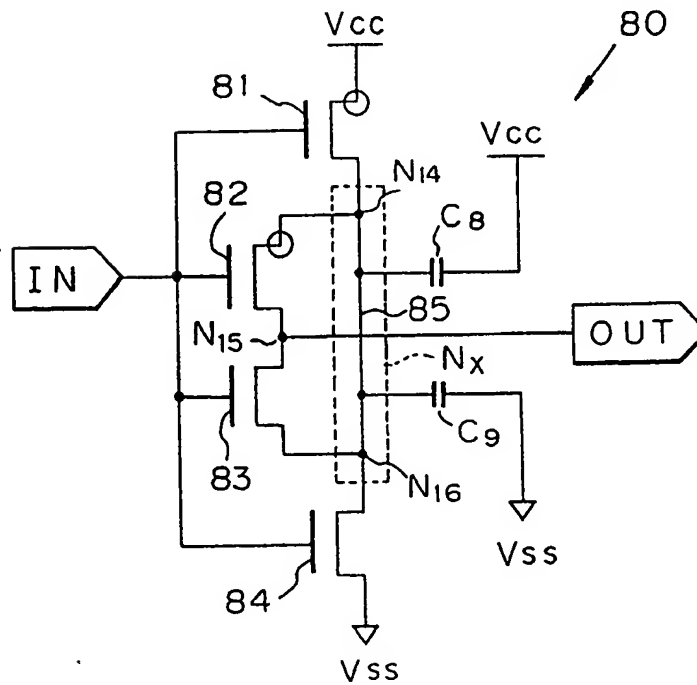


Fig. 15

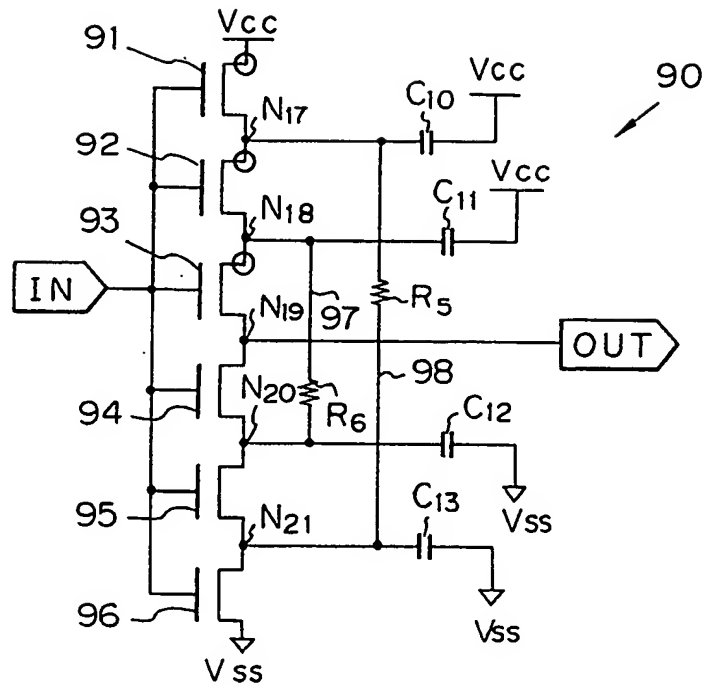


Fig. 16

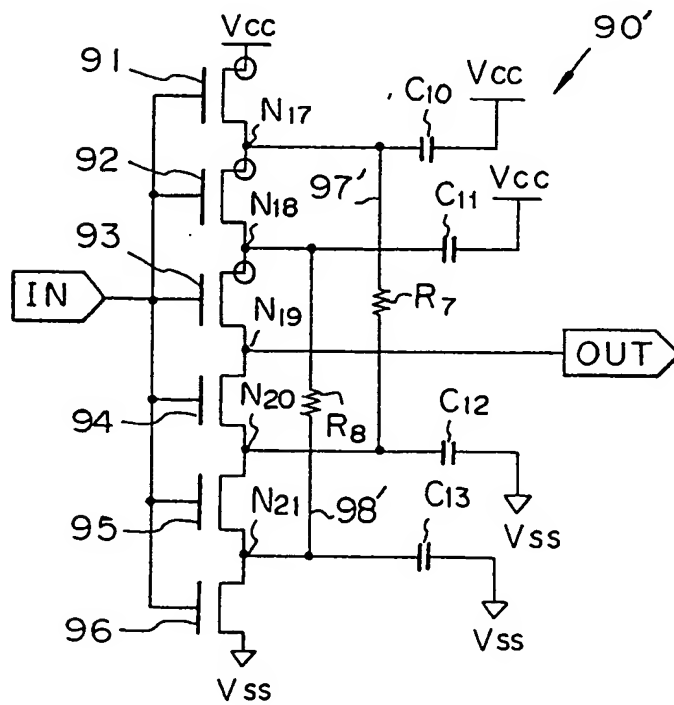
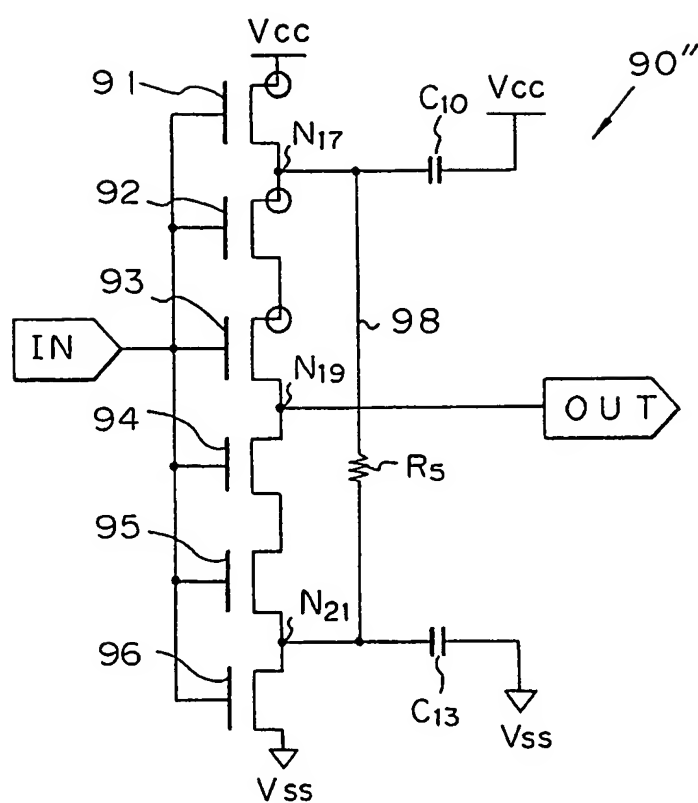


Fig. 17



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